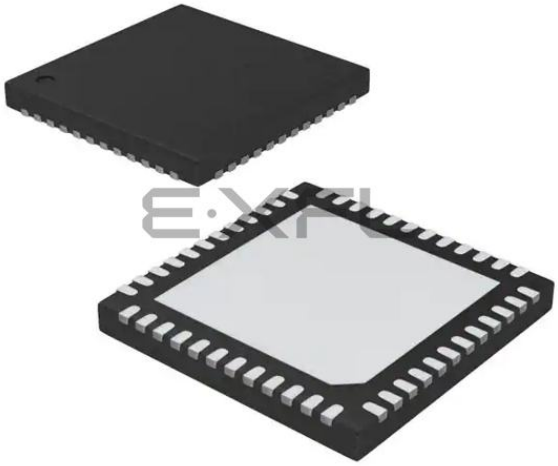

Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	768
Total RAM Bits	-
Number of I/O	34
Number of Gates	30000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	48-VFQFN Exposed Pad
Supplier Device Package	48-QFN (6x6)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agl030v2-qng48

User Nonvolatile FlashROM

IGLOO devices have 1 kbit of on-chip, user-accessible, nonvolatile FlashROM. The FlashROM can be used in diverse system applications:

- Internet protocol addressing (wireless or fixed)
- System calibration settings
- Device serialization and/or inventory control
- Subscription-based business models (for example, set-top boxes)
- Secure key storage for secure communications algorithms
- Asset management/tracking
- Date stamping
- Version management

The FlashROM is written using the standard IGLOO IEEE 1532 JTAG programming interface. The core can be individually programmed (erased and written), and on-chip AES decryption can be used selectively to securely load data over public networks (except in the AGL015 and AGL030 devices), as in security keys stored in the FlashROM for a user design.

The FlashROM can be programmed via the JTAG programming interface, and its contents can be read back either through the JTAG programming interface or via direct FPGA core addressing. Note that the FlashROM can only be programmed from the JTAG interface and cannot be programmed from the internal logic array.

The FlashROM is programmed as 8 banks of 128 bits; however, reading is performed on a byte-by-byte basis using a synchronous interface. A 7-bit address from the FPGA core defines which of the 8 banks and which of the 16 bytes within that bank are being read. The three most significant bits (MSBs) of the FlashROM address determine the bank, and the four least significant bits (LSBs) of the FlashROM address define the byte.

The Microsemi development software solutions, Libero® System-on-Chip (SoC) and Designer, have extensive support for the FlashROM. One such feature is auto-generation of sequential programming files for applications requiring a unique serial number in each part. Another feature allows the inclusion of static data for system version control. Data for the FlashROM can be generated quickly and easily using Libero SoC and Designer software tools. Comprehensive programming file support is also included to allow for easy programming of large numbers of parts with differing FlashROM contents.

SRAM and FIFO

IGLOO devices (except the AGL015 and AGL030 devices) have embedded SRAM blocks along their north and south sides. Each variable-aspect-ratio SRAM block is 4,608 bits in size. Available memory configurations are 256×18, 512×9, 1k×4, 2k×2, and 4k×1 bits. The individual blocks have independent read and write ports that can be configured with different bit widths on each port. For example, data can be sent through a 4-bit port and read as a single bitstream. The embedded SRAM blocks can be initialized via the device JTAG port (ROM emulation mode) using the UJTAG macro (except in the AGL015 and AGL030 devices).

In addition, every SRAM block has an embedded FIFO control unit. The control unit allows the SRAM block to be configured as a synchronous FIFO without using additional core VersaTiles. The FIFO width and depth are programmable. The FIFO also features programmable Almost Empty (AEMPTY) and Almost Full (AFULL) flags in addition to the normal Empty and Full flags. The embedded FIFO control unit contains the counters necessary for generation of the read and write address pointers. The embedded SRAM/FIFO blocks can be cascaded to create larger configurations.

PLL and CCC

IGLOO devices provide designers with very flexible clock conditioning circuit (CCC) capabilities. Each member of the IGLOO family contains six CCCs. One CCC (center west side) has a PLL. The AGL015 and AGL030 do not have a PLL.

The six CCC blocks are located at the four corners and the centers of the east and west sides. One CCC (center west side) has a PLL.

All six CCC blocks are usable; the four corner CCCs and the east CCC allow simple clock delay operations as well as clock spine access.

The inputs of the six CCC blocks are accessible from the FPGA core or from one of several inputs located near the CCC that have dedicated connections to the CCC block.

The CCC block has these key features:

User I/O Characteristics

Timing Model

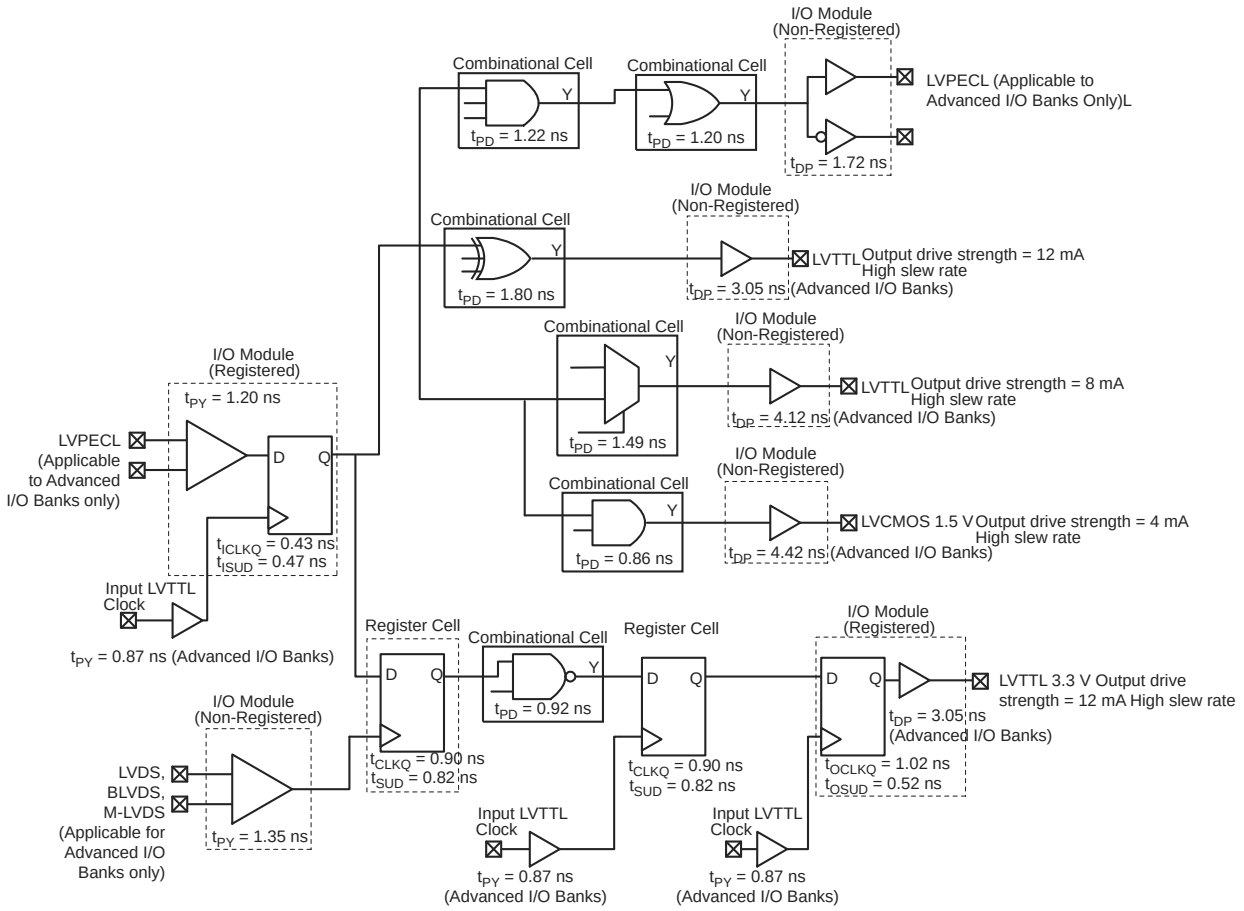

Figure 2-3 • **Timing Model**
Operating Conditions: Std. Speed, Commercial Temperature Range (T_J = 70°C), Worst-Case VCC = 1.425 V, for DC 1.5 V Core Voltage, Applicable to V2 and V5 Devices

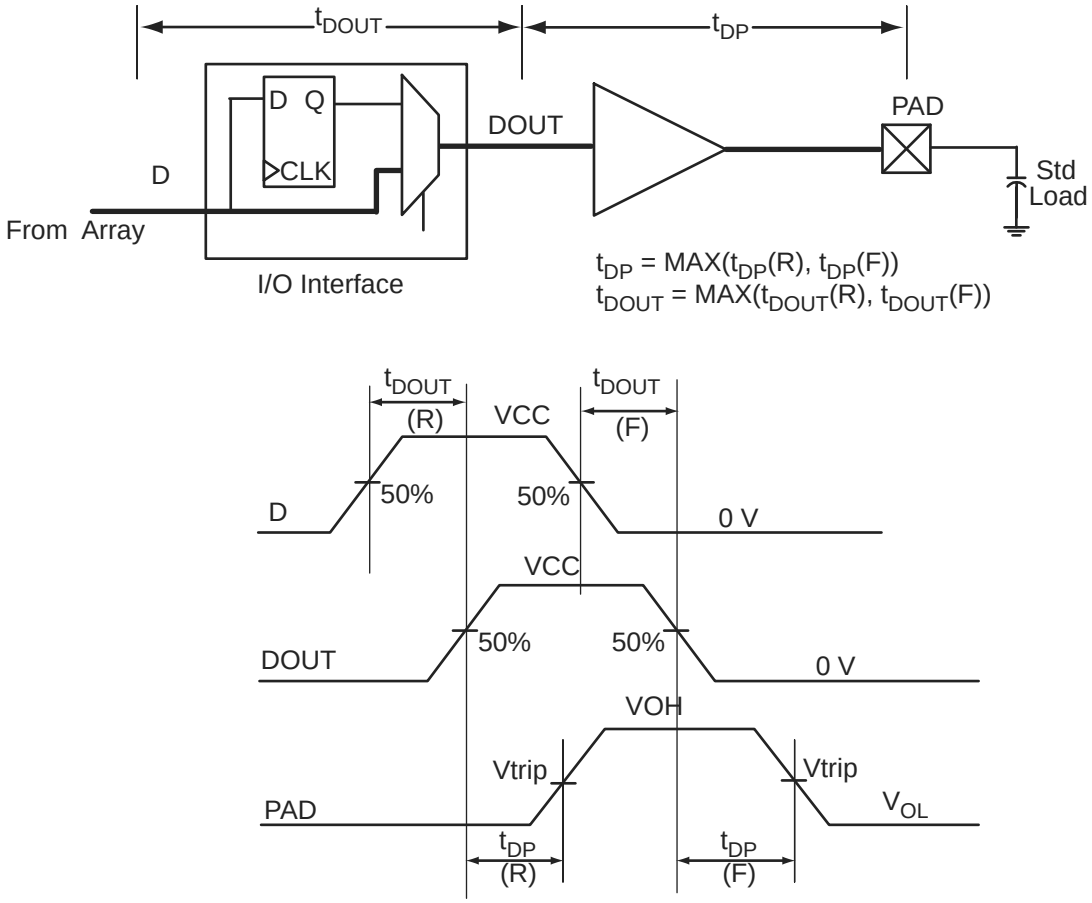

Figure 2-5 • **Output Buffer Model and Delays (example)**

Table 2-27 • **Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings**
Applicable to Standard I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[2]	Slew Rate	VIL		V_{IH}		VOL	V_{OH}	I_{OL}[1]	I_{OH}[1]
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	8 mA	High	–0.3	0.8	2	3.6	0.4	2.4	8	8
3.3 V LVCMOS Wide Range[3]	100 µA	8 mA	High	–0.3	0.8	2	3.6	0.2	VDD-0.2	0.1	0.1
2.5 V LVCMOS	8 mA	8 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	8	8
1.8 V LVCMOS	4 mA	4 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4
1.5 V LVCMOS	2 mA	2 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS[4]	1 mA	1 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	1	1
1.2 V LVCMOS Wide Range[4,5]	100 µA	1 mA	High	–0.3	0.3 * VCCI	0.7 * VCCI	3.6	0.1	VCCI – 0.1	0.1	0.1

Notes:

1. *Currents are measured at 85°C junction temperature.*
2. *The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
3. *All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
4. *Applicable to V2 Devices operating at VCCI ≥ VCC.*
5. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.*

Table 2-36 • Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst-Case V_{CC} = 1.14 V, Worst-Case VCCI (per standard) Applicable to Standard I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[1] (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	8	High	5	–	1.55	2.38	0.26	0.94	1.10	2.41	1.92	2.40	2.96	ns
3.3 V LVCMOS Wide Range[3]	100 µA	8	High	5	–	1.55	3.33	0.26	1.29	1.10	3.33	2.62	3.34	4.07	ns
2.5 V LVCMOS	8 mA	8	High	5	–	1.55	2.39	0.26	1.15	1.10	2.42	2.05	2.38	2.80	ns
1.8 V LVCMOS	4 mA	4	High	5	–	1.55	2.60	0.26	1.08	1.10	2.64	2.33	2.38	2.62	ns
1.5 V LVCMOS	2 mA	2	High	5	–	1.55	2.92	0.26	1.22	1.10	2.96	2.60	2.40	2.56	ns
1.2 V LVCMOS	1 mA	1	High	5	–	1.55	3.59	0.26	1.53	1.10	3.47	3.06	2.51	2.49	ns
1.2 V LVCMOS Wide Range[3]	100 µA	1	High	5	–	1.55	3.59	0.26	1.53	1.10	3.47	3.06	2.51	2.49	ns

Notes:

1. *The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
3. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification*
4. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-44 • **I/O Short Currents IOSH/IOSL Applicable to Standard I/O Banks**

	Drive Strength	IOSL (mA)*	IOSH (mA)*
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	25	27
	4 mA	25	27
	6 mA	51	54
	8 mA	51	54
3.3 V LVCMOS Wide Range	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	16	18
	4 mA	16	18
	6 mA	32	37
	8 mA	32	37
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
1.5 V LVCMOS	2 mA	13	16
1.2 V LVCMOS	1 mA	20	26
1.2 V LVCMOS Wide Range	100 µA	20	26

*Note: *T_J = 100°C*

The length of time an I/O can withstand I_{OSH}/I_{OSL} events depends on the junction temperature. The reliability data below is based on a 3.3 V, 12 mA I/O setting, which is the worst case for this type of analysis.

For example, at 100°C, the short current condition would have to be sustained for more than six months to cause a reliability concern. The I/O design does not contain any short circuit protection, but such protection would only be needed in extremely prolonged stress conditions.

Table 2-45 • **Duration of Short Circuit Event before Failure**

Temperature	Time before Failure
–40°C	> 20 years
–20°C	> 20 years
0°C	> 20 years
25°C	> 20 years
70°C	5 years
85°C	2 years
100°C	6 months

Table 2-46 • **I/O Input Rise Time, Fall Time, and Related I/O Reliability1**

Input Buffer	Input Rise/Fall Time (min.)	Input Rise/Fall Time (max.)	Reliability
LVTTL/LVCMOS	No requirement	10 ns *	20 years (100°C)
LVDS/B-LVDS/M-LVDS/ LVPECL	No requirement	10 ns *	10 years (100°C)

Note: The maximum input rise/fall time is related to the noise induced into the input buffer trace. If the noise is low, then the rise time and fall time of input buffers can be increased beyond the maximum value. The longer the rise/fall times, the more susceptible the input signal is to the board noise. Microsemi recommends signal integrity evaluation/characterization of the system to ensure that there is no excessive noise coupling into input signals.

Table 2-107 • **1.8 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V
Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	6.32	0.26	1.11	1.10	6.43	5.81	2.47	2.16	12.22	11.60	ns
4 mA	Std.	1.55	5.27	0.26	1.11	1.10	5.35	5.01	2.78	2.92	11.14	10.79	ns
6 mA	Std.	1.55	4.56	0.26	1.11	1.10	4.64	4.44	3.00	3.30	10.42	10.22	ns
8 mA	Std.	1.55	4.56	0.26	1.11	1.10	4.64	4.44	3.00	3.30	10.42	10.22	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-108 • **1.8 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V
Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.22	0.26	1.11	1.10	3.26	3.18	2.47	2.20	9.05	8.97	ns
4 mA	Std.	1.55	2.72	0.26	1.11	1.10	2.75	2.50	2.78	3.01	8.54	8.29	ns
6 mA	Std.	1.55	2.43	0.26	1.11	1.10	2.47	2.16	2.99	3.39	8.25	7.94	ns
8 mA	Std.	1.55	2.43	0.26	1.11	1.10	2.47	2.16	2.99	3.39	8.25	7.94	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.*

Table 2-109 • **1.8 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	6.13	0.26	1.08	1.10	6.24	5.79	2.08	1.78	ns
4 mA	Std.	1.55	5.17	0.26	1.08	1.10	5.26	4.98	2.38	2.54	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-110 • **1.8 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	3.06	0.26	1.08	1.10	3.10	3.01	2.08	1.83	3.06	ns
4 mA	Std.	2.60	0.26	1.08	1.10	2.64	2.33	2.38	2.62	2.60	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.*

Table 2-119 • 1.5 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.97	5.88	0.18	1.14	0.66	6.00	5.45	2.00	1.94	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-120 • 1.5 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.4 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.97	2.51	0.18	1.14	0.66	2.56	2.21	1.99	2.03	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

1.2 V DC Core Voltage

Table 2-121 • 1.5 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	7.17	0.26	1.27	1.10	7.29	6.60	3.33	3.03	13.07	12.39	ns
4 mA	Std.	1.55	6.27	0.26	1.27	1.10	6.37	5.86	3.61	3.51	12.16	11.64	ns
6 mA	Std.	1.55	5.94	0.26	1.27	1.10	6.04	5.70	3.67	3.64	11.82	11.48	ns
8 mA	Std.	1.55	5.86	0.26	1.27	1.10	5.96	5.71	2.83	4.11	11.74	11.50	ns
12 mA	Std.	1.55	5.86	0.26	1.27	1.10	5.96	5.71	2.83	4.11	11.74	11.50	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-122 • 1.5 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.4 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.44	0.26	1.27	1.10	3.49	3.35	3.32	3.12	9.28	9.14	ns
4 mA	Std.	1.55	3.06	0.26	1.27	1.10	3.10	2.89	3.60	3.61	8.89	8.67	ns
6 mA	Std.	1.55	2.98	0.26	1.27	1.10	3.02	2.80	3.66	3.74	8.81	8.58	ns
8 mA	Std.	1.55	2.96	0.26	1.27	1.10	3.00	2.70	3.75	4.23	8.78	8.48	ns
12 mA	Std.	1.55	2.96	0.26	1.27	1.10	3.00	2.70	3.75	4.23	8.78	8.48	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.*

Table 2-135 • **1.2 V LVCMOS High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
1 mA	Std.	1.55	8.57	0.26	1.53	1.10	8.23	7.38	2.51	2.39	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-136 • **1.2 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
1 mA	Std.	1.55	3.59	0.26	1.53	1.10	3.47	3.06	2.51	2.49	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.*

1.2 V LVCMOS Wide Range

Table 2-137 • **Minimum and Maximum DC Input and Output Levels for LVCMOS 1.2 V Wide Range**
Applicable to Advanced I/O Banks

1.2 V LVCMOS Wide Range		VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[2]	IIH[3]
Drive Strength	Equivalent Software Default Drive Strength Option[1]	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[4]	Max. mA[4]	µA[5]	µA[5]
100 µA	2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.26	0.25 * VCCI	0.75 * VCCI	100	100	20	26	10	10

Notes:

1. *The minimum drive strength for the default LVCMOS 1.2 V software configuration when run in wide range is ± 100 µA. The drive strength displayed in software is supported in normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
3. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
4. *Currents are measured at 100°C junction temperature and maximum voltage.*
5. *Currents are measured at 85°C junction temperature.*
6. *Software default selection highlighted in gray.*

3.3 V PCI, 3.3 V PCI-X

Peripheral Component Interface for 3.3 V standard specifies support for 33 MHz and 66 MHz PCI Bus applications.

Table 2-141 • Minimum and Maximum DC Input and Output Levels Applicable to Advanced and Standard Plus I/Os

3.3 V PCI/PCI-X	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[1]	Max. mA[1]	µA[2]	µA[2]
Per PCI specification	Per PCI curves										10	10

Notes:

1. *Currents are measured at 100°C junction temperature and maximum voltage.*
2. *Currents are measured at 85°C junction temperature.*

AC loadings are defined per the PCI/PCI-X specifications for the datapath; Microsemi loadings for enable path characterization are described in Figure 2-12.

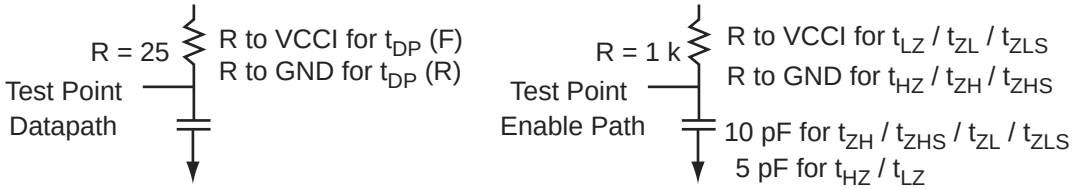

Figure 2-12 • AC Loading

AC loadings are defined per PCI/PCI-X specifications for the datapath; Microsemi loading for tristate is described in Table 2-142.

Table 2-142 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	3.3	0.285 * VCCI for $t_{DP(R)}$ 0.615 * VCCI for $t_{DP(F)}$	10

*Note: *Measuring point = Vtrip. See Table 2-29 on page 2-28 for a complete table of trip points.*

Timing Characteristics

1.5 V DC Core Voltage

Table 2-143 • 3.3 V PCI/PCI-X Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V Applicable to Advanced I/O Banks

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.97	2.32	0.19	0.70	0.66	2.37	1.78	2.67	3.05	5.96	5.38	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-144 • 3.3 V PCI/PCI-X Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V Applicable to Standard Plus I/O Banks

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
Std.	0.97	1.97	0.19	0.70	0.66	2.01	1.50	2.36	2.79	5.61	5.10	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Timing Characteristics

1.5 V DC Core Voltage

Table 2-169 • Combinatorial Cell Propagation Delays
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Combinatorial Cell	Equation	Parameter	Std.	Units
INV	Y =!A	t_{PD}	0.80	ns
AND2	Y = A · B	t_{PD}	0.84	ns
NAND2	Y =!(A · B)	t_{PD}	0.90	ns
OR2	Y = A + B	t_{PD}	1.19	ns
NOR2	Y = !(A + B)	t_{PD}	1.10	ns
XOR2	Y = A ⊕ B	t_{PD}	1.37	ns
MAJ3	Y = MAJ(A, B, C)	t_{PD}	1.33	ns
XOR3	Y = A ⊕ B ⊕ C	t_{PD}	1.79	ns
MUX2	Y = A !S + B S	t_{PD}	1.48	ns
AND3	Y = A · B · C	t_{PD}	1.21	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

1.2 V DC Core Voltage

Table 2-170 • Combinatorial Cell Propagation Delays
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Combinatorial Cell	Equation	Parameter	Std.	Units
INV	Y = !A	t_{PD}	1.34	ns
AND2	Y = A · B	t_{PD}	1.43	ns
NAND2	Y = !(A · B)	t_{PD}	1.59	ns
OR2	Y = A + B	t_{PD}	2.30	ns
NOR2	Y = !(A + B)	t_{PD}	2.07	ns
XOR2	Y = A ⊕ B	t_{PD}	2.46	ns
MAJ3	Y = MAJ(A, B, C)	t_{PD}	2.46	ns
XOR3	Y = A ⊕ B ⊕ C	t_{PD}	3.12	ns
MUX2	Y = A !S + B S	t_{PD}	2.83	ns
AND3	Y = A · B · C	t_{PD}	2.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

1.2 V DC Core Voltage

Table 2-181 • AGL015 Global Resource
Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	1.79	2.09	ns
t_{RCKH}	Input High Delay for Global Clock	1.87	2.26	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.39	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-182 • AGL030 Global Resource
Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	1.80	2.09	ns
t_{RCKH}	Input High Delay for Global Clock	1.88	2.27	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.40		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.39	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Clock Conditioning Circuits

CCC Electrical Specifications

Timing Characteristics

Table 2-189 • IGLOO CCC/PLL Specification
For IGLOO V2 or V5 Devices, 1.5 V DC Core Supply Voltage

Parameter	Min.	Typ.	Max.	Units
Clock Conditioning Circuitry Input Frequency f_{IN_CCC}	1.5		250	MHz
Clock Conditioning Circuitry Output Frequency f_{OUT_CCC}	0.75		250	MHz
Delay Increments in Programmable Delay Blocks [1, 2]		360[3]		ps
Number of Programmable Values in Each Programmable Delay Block			32	
Serial Clock (SCLK) for Dynamic PLL[4, 5]			100	ns
Input Cycle-to-Cycle Jitter (peak magnitude)			1	ns
Acquisition Time				
LockControl = 0			300	µs
LockControl = 1			6.0	ms
Tracking Jitter[6]				
LockControl = 0			2.5	ns
LockControl = 1			1.5	ns
Output Duty Cycle	48.5		51.5	%
Delay Range in Block: Programmable Delay 1 [1, 2]	1.25		15.65	ns
Delay Range in Block: Programmable Delay 2 [1, 2]	0.469		15.65	ns
Delay Range in Block: Fixed Delay [1, 2]		3.5		ns
CCC Output Peak-to-Peak Period Jitter F_{CCC_OUT}	Maximum Peak-to-Peak Jitter Data[7]			
	SSO ≥ 4[8]	SSO ≥ 8[8]	SSO ≥ 16[8]	
0.75 MHz to 50 MHz	0.60%	0.80%	1.20%	
50 MHz to 160 MHz	4.00%	6.00%	12.00%	

Notes:

1. *This delay is a function of voltage and temperature. See Table 2-6 on page 2-7 and Table 2-7 on page 2-7 for deratings.*
2. *T_J = 25°C, V_{CC} = 1.5 V*
3. *When the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available. Refer to the Libero SoC Online Help associated with the core for more information.*
4. *The AGL030 device does not support a PLL.*
5. *Maximum value obtained for a Std. speed grade device in Worst-Case Commercial Conditions. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*
6. *Tracking jitter is defined as the variation in clock edge position of PLL outputs with reference to the PLL input clock edge. Tracking jitter does not measure the variation in PLL output period, which is covered by the period jitter parameter.*
7. *Measurements done with LVTTL 3.3 V, 8 mA I/O drive strength, and high slew Rate. VCC/VCCPLL = 1.14 V, VQ/PQ/TQ type of packages, 20 pF load.*
8. *Simultaneously Switching Outputs (SSOs) are outputs that are synchronous to a single clock domain and have clock-to-out times that are within ±200 ps of each other. Switching I/Os are placed outside of the PLL bank. Refer to the "Simultaneously Switching Outputs (SSOs) and Printed Circuit Board Layout" section in the IGLOO FPGA Fabric User Guide.*

1.2 V DC Core Voltage

***Table 2-196* • FIFO**
Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.	Units
t_{ENS}	REN, WEN Setup Time	4.13	ns
t_{ENH}	REN, WEN Hold Time	0.31	ns
t_{BKS}	BLK Setup Time	0.47	ns
t_{BKH}	BLK Hold Time	0.00	ns
t_{DS}	Input Data (WD) Setup Time	1.56	ns
t_{DH}	Input Data (WD) Hold Time	0.49	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	6.80	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	3.62	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	7.23	ns
t_{WCKFF}	WCLK High to Full Flag Valid	6.85	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	26.61	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	7.12	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	26.33	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	4.09	ns
	RESET Low to Data Out Low on RD (pipelined)	4.09	ns
$t_{REMRSTB}$	RESET Removal	1.23	ns
$t_{RECRSTB}$	RESET Recovery	6.58	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	1.18	ns
t_{CYC}	Clock Cycle Time	10.90	ns
F_{MAX}	Maximum Frequency for FIFO	92	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

CS81	
Pin Number	**AGL250 Function**
A1	GAA0/IO00RSB0
A2	GAA1/IO01RSB0
A3	GAC0/IO04RSB0
A4	IO13RSB0
A5	IO21RSB0
A6	IO27RSB0
A7	GBB0/IO37RSB0
A8	GBA1/IO40RSB0
A9	GBA2/IO41PPB1
B1	GAA2/IO118UPB3
B2	GAB0/IO02RSB0
B3	GAC1/IO05RSB0
B4	IO11RSB0
B5	IO23RSB0
B6	GBC0/IO35RSB0
B7	GBB1/IO38RSB0
B8	IO41NPB1
B9	GBB2/IO42PSB1
C1	GAB2/IO117UPB3
C2	IO118VPB3
C3	GND
C4	IO15RSB0
C5	IO25RSB0
C6	GND
C7	GBA0/IO39RSB0
C8	GBC2/IO43PDB1
C9	IO43NDB1
D1	GAC2/IO116USB3
D2	IO117VPB3
D3	GFA2/IO107PSB3
D4	VCC
D5	VCCIB0
D6	GND
D7	IO52NPB1
D8	GCC1/IO48PDB1
D9	GCC0/IO48NDB1

CS81	
Pin Number	**AGL250 Function**
E1	GFB0/IO109NDB3
E2	GFB1/IO109PDB3
E3	GFA1/IO108PSB3
E4	VCCIB3
E5	VCC
E6	VCCIB1
E7	GCA0/IO50NDB1
E8	GCA1/IO50PDB1
E9	GCB2/IO52PPB1
F1	VCCPLF
F2	VCOMPLF
F3	GND
F4	GND
F5	VCCIB2
F6	GND
F7	GDA1/IO60USB1
F8	GDC1/IO58UDB1
F9	GDC0/IO58VDB1
G1	GEA0/IO98NDB3
G2	GEC1/IO100PDB3
G3	GEC0/IO100NDB3
G4	IO91RSB2
G5	IO86RSB2
G6	IO71RSB2
G7	GDB2/IO62RSB2
G8	VJTAG
G9	TRST
H1	GEA1/IO98PDB3
H2	FF/GEB2/IO96RSB2
H3	IO93RSB2
H4	IO90RSB2
H5	IO85RSB2
H6	IO77RSB2
H7	GDA2/IO61RSB2
H8	TDI
H9	TDO

CS81	
Pin Number	**AGL250 Function**
J1	GEA2/IO97RSB2
J2	GEC2/IO95RSB2
J3	IO92RSB2
J4	IO88RSB2
J5	IO84RSB2
J6	IO74RSB2
J7	TCK
J8	TMS
J9	VPUMP

CS196	
Pin Number	**AGL250 Function**
A1	GND
A2	GAA0/IO00RSB0
A3	GAC0/IO04RSB0
A4	GAC1/IO05RSB0
A5	IO10RSB0
A6	IO13RSB0
A7	IO17RSB0
A8	IO19RSB0
A9	IO23RSB0
A10	GBC0/IO35RSB0
A11	GBB0/IO37RSB0
A12	GBB1/IO38RSB0
A13	GBA1/IO40RSB0
A14	GND
B1	VCCIB3
B2	VMV0
B3	GAA1/IO01RSB0
B4	GAB1/IO03RSB0
B5	GND
B6	IO12RSB0
B7	IO16RSB0
B8	IO22RSB0
B9	IO24RSB0
B10	GND
B11	GBC1/IO36RSB0
B12	GBA0/IO39RSB0
B13	GBA2/IO41PPB1
B14	GBB2/IO42PDB1
C1	GAC2/IO116UDB3
C2	GAB2/IO117UDB3
C3	GNDQ
C4	VCCIB0
C5	GAB0/IO02RSB0
C6	IO11RSB0
C7	VCCIB0
C8	IO20RSB0

CS196	
Pin Number	**AGL250 Function**
C9	IO30RSB0
C10	IO33RSB0
C11	VCCIB0
C12	IO41NPB1
C13	GNDQ
C14	IO42NDB1
D1	IO116VDB3
D2	IO117VDB3
D3	GAA2/IO118UDB3
D4	IO113PPB3
D5	IO08RSB0
D6	IO14RSB0
D7	IO15RSB0
D8	IO18RSB0
D9	IO25RSB0
D10	IO32RSB0
D11	IO44PPB1
D12	VMV1
D13	IO43NDB1
D14	GBC2/IO43PDB1
E1	IO112PDB3
E2	GND
E3	IO118VDB3
E4	VCCIB3
E5	IO114USB3
E6	IO07RSB0
E7	IO09RSB0
E8	IO21RSB0
E9	IO31RSB0
E10	IO34RSB0
E11	VCCIB1
E12	IO44NPB1
E13	GND
E14	IO45PDB1
F1	IO112NDB3
F2	IO107NPB3

CS196	
Pin Number	**AGL250 Function**
F3	IO111PDB3
F4	IO111NDB3
F5	IO113NPB3
F6	IO06RSB0
F7	VCC
F8	VCC
F9	IO28RSB0
F10	IO54PDB1
F11	IO54NDB1
F12	IO47NDB1
F13	IO47PDB1
F14	IO45NDB1
G1	GFB1/IO109PDB3
G2	GFA0/IO108NDB3
G3	GFA2/IO107PPB3
G4	VCOMPLF
G5	GFC0/IO110NDB3
G6	VCC
G7	GND
G8	GND
G9	VCC
G10	GCC0/IO48NDB1
G11	GCB1/IO49PDB1
G12	GCA0/IO50NDB1
G13	IO53NDB1
G14	GCC2/IO53PDB1
H1	GFB0/IO109NDB3
H2	GFA1/IO108PDB3
H3	VCCPLF
H4	GFB2/IO106PPB3
H5	GFC1/IO110PDB3
H6	VCC
H7	GND
H8	GND
H9	VCC
H10	GCC1/IO48PDB1

QN132	
Pin Number	**AGL250 Function**
C17	IO74RSB2
C18	VCCIB2
C19	TCK
C20	VMV2
C21	VPUMP
C22	VJTAG
C23	VCCIB1
C24	IO53NSB1
C25	IO51NPB1
C26	GCA1/IO50PPB1
C27	GCC0/IO48NDB1
C28	VCCIB1
C29	IO42NDB1
C30	GNDQ
C31	GBA1/IO40RSB0
C32	GBB0/IO37RSB0
C33	VCC
C34	IO24RSB0
C35	IO19RSB0
C36	IO16RSB0
C37	IO10RSB0
C38	VCCIB0
C39	GAB1/IO03RSB0
C40	VMV0
D1	GND
D2	GND
D3	GND
D4	GND

FG484	
Pin Number	**AGL400 Function**
R9	VCCIB2
R10	VCCIB2
R11	IO108RSB2
R12	IO101RSB2
R13	VCCIB2
R14	VCCIB2
R15	VMV2
R16	IO83RSB2
R17	GDB1/IO78UPB1
R18	GDC1/IO77UDB1
R19	IO75NDB1
R20	VCC
R21	NC
R22	NC
T1	NC
T2	NC
T3	NC
T4	IO140NDB3
T5	IO138PPB3
T6	GEC1/IO137PPB3
T7	IO131RSB2
T8	GNDQ
T9	GEA2/IO134RSB2
T10	IO117RSB2
T11	IO111RSB2
T12	IO99RSB2
T13	IO94RSB2
T14	IO87RSB2
T15	GNDQ
T16	IO93RSB2
T17	VJTAG
T18	GDC0/IO77VDB1
T19	GDA1/IO79UDB1
T20	NC
T21	NC
T22	NC

FG484	
Pin Number	**AGL1000 Function**
H19	IO87PDB1
H20	VCC
H21	NC
H22	NC
J1	IO212NDB3
J2	IO212PDB3
J3	NC
J4	IO217NDB3
J5	IO218NDB3
J6	IO216PDB3
J7	IO216NDB3
J8	VCCIB3
J9	GND
J10	VCC
J11	VCC
J12	VCC
J13	VCC
J14	GND
J15	VCCIB1
J16	IO83NPB1
J17	IO86NPB1
J18	IO90PPB1
J19	IO87NDB1
J20	NC
J21	IO89PDB1
J22	IO89NDB1
K1	IO211PDB3
K2	IO211NDB3
K3	NC
K4	IO210PPB3
K5	IO213NDB3
K6	IO213PDB3
K7	GFC1/IO209PPB3
K8	VCCIB3
K9	VCC
K10	GND

Revision / Version	Changes	Page
Advance v0.4 (September 2007)	Cortex-M1 device information was added to Table 1 • IGLOO Product Family, the "I/Os Per Package1" table, "IGLOO Ordering Information", and Temperature Grade Offerings.	i, ii, iii, iv
	The number of single-ended I/Os for the CS81 package for AGL030 was updated to 66 in the "I/Os Per Package1" table.	ii
	The "Power Conservation Techniques" section was updated to recommend that unused I/O signals be left floating.	2-51
Advance v0.3 (August 2007)	In Table 1 • IGLOO Product Family, the CS81 package was added for AGL030. The CS196 was replaced by the CS121 for AGL060. Table note 3 was moved to the specific packages to which it applies for AGL060: QN132 and FG144.	i
	The CS81 and CS121 packages were added to the "I/Os Per Package1" table. The number of single-ended I/Os was removed for the CS196 package in AGL060. Table note 6 was moved to the specific packages to which it applies for AGL060: QN132 and FG144.	ii
	The CS81 and CS121 packages were added to the Temperature Grade Offerings table. The temperature grade offerings were removed for the CS196 package in AGL060. Table note 3 was moved to the specific packages to which it applies for AGL060: QN132 and FG144.	iv
	The CS81 and CS121 packages were added to Table 2-31 • Flash*Freeze Pin Location in IGLOO Family Packages (device-independent).	2-61
Advance v0.2	The words "ambient temperature" were added to the temperature range in the "IGLOO Ordering Information", Temperature Grade Offerings, and "Speed Grade and Temperature Grade Matrix" sections.	iii, iv
	The T_J parameter in Table 3-2 • Recommended Operating Conditions was changed to T_A, ambient temperature, and table notes 4–6 were added.	3-2